

**IN THE CLAIMS:**

1.-18. (Cancel)

19. (Original) A magnetic recording sensor having a structure comprising a plurality of cells in parallel including a magnetoresistive sensor for recording information, a bit line connected to the magnetoresistive sensor for flowing an electric current to the sensor, a word line in the position opposite the bit line by interposing therebetween the magnetoresistive sensor layer and in the position away from the magnetoresistive sensor layer for performing recording operation onto the magnetoresistive sensor layer orthogonally to the bit line, an amplifying system for amplifying a read signal, and a read word line for switching between read and write, wherein the magnetoresistive sensor comprises the magnetoresistive sensor layer, and a layer for magnetic domain-controlling the magnetoresistive sensor layer is provided with the magnetic domain control layer having high electric resistance not less than 10 mΩcm.